

30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	Max R _{DS(ON)}	Max I _D T _A = +25°C (Note 6)
-30V	$70m\Omega$ @ $V_{GS} = -10V$	-4A

Description and Applications

This new generation of TRENCH MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

- DC DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

Features and Benefits

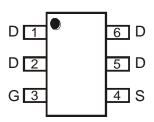
- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

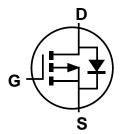
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 3
- Weight: 0.016 grams (Approximate)







Pin-Out (Top View)



Equivalent Circuit

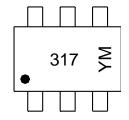
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inch)	Tape Width (mm)	Quantity Per Reel
ZXMP3A17E6TA	317	7	8	3000
ZXMP3A17E6TC	317	13	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



317 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022
Code	С	D	E	F	G	Н	I	J

Γ	Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
	Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

	Characteristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GS}	±20	V
		T _A = +25°C (Note 6)	l _D	-4.0	
Continuous Drain Current	$V_{GS} = -10V$	T _A = +70°C (Note 6)		-3.2	Α
		T _A = +25°C (Note 5)		-3.2	
Pulsed Drain Current (Note	7)		I _{DM}	-14.4	Α
Continuous Source Current	(Body Diode) (N	ote 6)	Is	-2.5	Α
Pulsed Source Current (Bod	ly Diode) (Note	7)	I _{SM}	-14.4	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = +25°C (Note 5) Linear derating factor	P _D	1.1 8.8	W mW/°C
Power Dissipation at T _A = +25°C (Note 6) Linear Derating Factor	P _D	1.7 13.6	W mW/°C
Junction to Ambient (Note 5)	$R_{ hetaJA}$	113	°C/W
Junction to Ambient (Note 6)	$R_{ hetaJA}$	73	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.

6. For a device surface mounted on FR-4 PCB measured at $t \le 5$ secs.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-30	-	-	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	-0.5	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}	-	=	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
Gate-Source Threshold Voltage	V _{GS(TH)}	-1.0	=	-	V	$I_D = -250 \mu A, V_{DS} = V_{GS}$	
Static Drain-Source On-State Resistance (Note 8)	R _{DS(ON)}	-	-	0.070	Ω	V _{GS} = -10V, I _D =-3.2A	
Citatio Brain Godino On Citato Nociotarios (Noto o)	TCDS(ON)			0.110		$V_{GS} = -4.5V, I_{D} = -2.5A$	
Forward Transconductance (Notes 8 &10)	g fs	-	6.4	-	S	$V_{DS} = -15V$, $I_{D} = -3.2A$	
Diode Forward Voltage (Note 8)	V_{SD}	-	-0.85	-1.2	V	T_{J} = +25°C , I_{S} = -2.5A, V_{GS} = 0V	
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 10)	Ciss	-	630	-	pF	\\\\ 45\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Output Capacitance (Note 10)	Coss	-	113	-	pF	$V_{DS} = -15V, V_{GS} = 0V$ - f = 1MHz	
Reverse Transfer Capacitance (Note 10)	C _{rss}	-	78	-	pF	I = IIVII IZ	
Gate Charge (Notes 9 &10)	Qg	-	8.28	-	nC	$V_{GS} = -5V, V_{DS} = -15V$ $I_{D} = -3.2A$	
Total Gate Charge (Notes 9 &10)	Q_g	-	15.8	-	nC	10)/)/ 45)/	
Gate-Source Charge (Notes 9 &10)	Qgs	-	1.84	-	nC	$V_{GS} = -10V, V_{DS} = -15V$ $-I_{D} = -3.2A$	
Gate-Drain Charge (Notes 9 &10)	Q _{qd}	-	2.8	-	nC	ID = -3.2A	
Turn-On Delay Time (Notes 9 &10)	t _{D(ON)}	-	1.74	-	ns		
Turn-On Rise Time (Notes 9 &10)	t _R	-	2.87	-	ns	V _{DD} = -15V, V _{GS} = -10V	
Turn-Off Delay Time (Notes 9 &10)	t _{D(OFF)}	-	29.2	-	ns	$I_D = -1A, R_G = 6.0\Omega$	
Turn-Off Fall Time (Notes 9 &10)	t _F	-	8.72	-	ns	1	
Reverse Recovery Time (Note 10)	t _{RR}	-	19.5	-	ns	T _J = +25°C, I _F =-1.7A,	
Reverse Recovery Charge (Note 10)	Q _{RR}	-	16.3	-	nC	di/dt= 100A/μs	

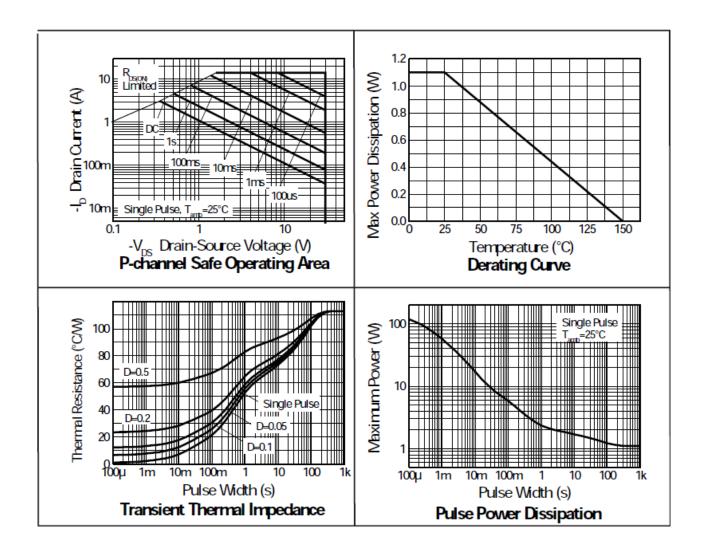
Notes: 8. Measured under pulsed conditions. Width=300 μ s. Duty cycle \leq 2%

10. For design aid only, not subject to production testing.

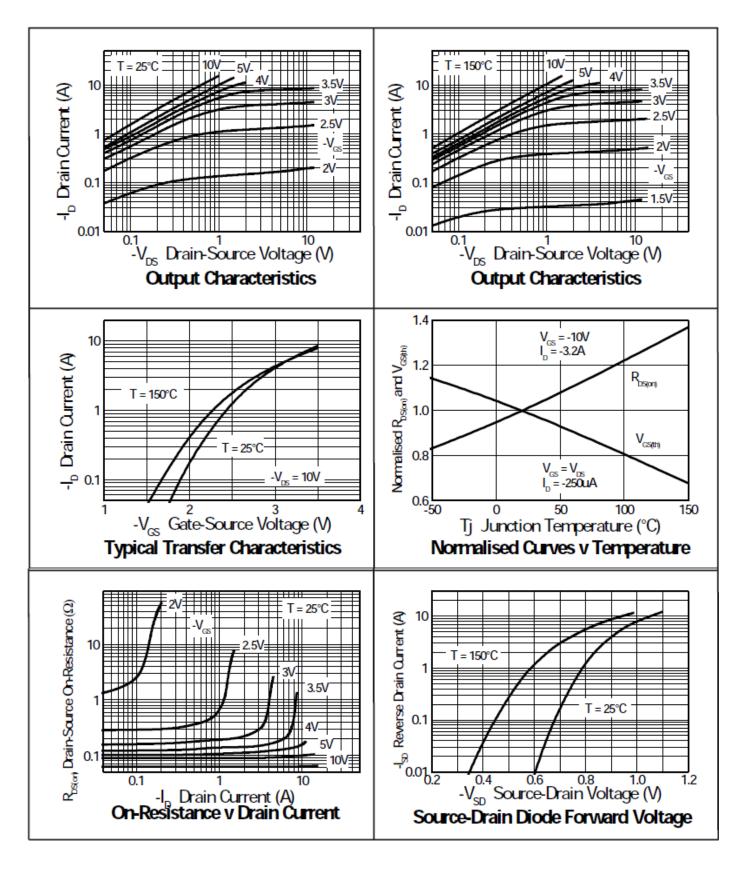
^{7.} Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05, pulse width 10µs - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

Switching characteristics are independent of operating junction temperature.

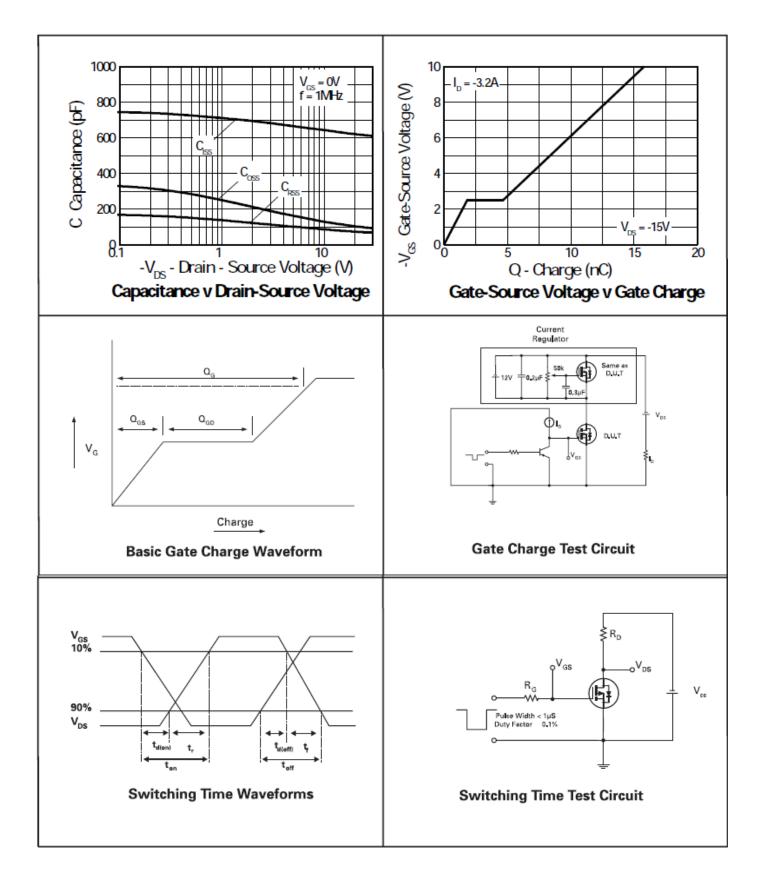








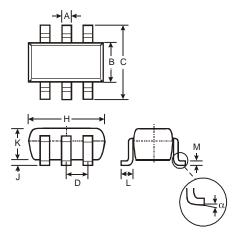






Package Outline Dimensions

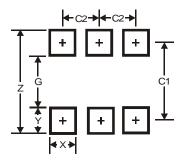
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT26								
Dim	Min	Max	Тур					
Α	0.35	0.50	0.38					
В	1.50	1.70	1.60					
С	2.70	3.00	2.80					
D	_	_	0.95					
Н	2.90	3.10	3.00					
J	0.013	0.10	0.05					
K	1.00	1.30	1.10					
L	0.35	0.55	0.40					
М	0.10	0.20	0.15					
α	0°	8°	_					
All Dimensions in mm								

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Υ	0.80
C1	2.40
C2	0.95



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